What is claimed is:

1. A manufacturing method for an electronic device, comprising:

a hole-forming step of forming a contact hole in an insulating film that covers a conductive part formed on a first main surface of a substrate and an area surrounding the conductive part, the hole being formed beside the conductive part, and the conductive part including a first material;

a material-supplying step of supplying a second material to the contact hole, the second material having a reactive property with the first material; and

an inspection step, after the second material has been supplied, of inspecting for evidence of a reaction by the conductive part with the second material.

2. The manufacturing method of Claim 1, wherein

the reactive property of the second material causes the conductive part to be eroded on contact with the second material, and

in the inspection step, evidence that the conductive part has been eroded is inspected for.

3. The manufacturing method of Claim 2, wherein

in the inspection step, evidence of erosion is inspected for optically.

4. The manufacturing method of Claim 3, wherein

in the inspection step, evidence of erosion is inspected for after removing the second material from the contact hole.

5. The manufacturing method of Claim 4, wherein

the first material is one of tungsten and a tungsten alloy, and

the second material is a solution including one of hydrogen peroxide and ozone.

6. The manufacturing method of Claim 5, wherein

in the material-supplying step, the solution is supplied to the contact hole under a condition by which the solution is able to selectively erode the conductive part.

7. The manufacturing method of Claim 1, wherein

the electronic device is a memory device that includes a plurality of components that function as field effect transistors, and

the conductive part is a function electrode that is formed before the hole-forming step by applying a design rule that

stipulates an electrode width of 0.18μm or less.

8. The manufacturing method of Claim 3, wherein

the conductive part includes a large-area portion that is sufficient in size to enable inspection thereof with an optical microscope for evidence of the reaction, and

in the inspection step, evidence of the reaction in the large-area portion is inspected for.

9. The manufacturing method of Claim 2, wherein

in the inspection step, after a material including at least the second material has been removed, presence of at least one of the first material and a compound of the first material and the second material is inspected for in the removed material.

10. The manufacturing method of Claim 1, wherein

the substrate has a pre-formed inspection area that is independent of other circuits areas,

in the material-supplying step a contact hole formed in the inspection area is subject to the inspection, and

in the inspection step, a conductive part formed in the inspection area is subject to the inspection.

11. The manufacturing method of Claim 1, wherein

in the hole forming step, the contact hole is formed using a self-align contact method.

12. The manufacturing method of Claim 11, wherein a silicon nitride film is provided on the substrate as an etching stopper layer in the hole forming step.

13. The manufacturing method of Claim 12, wherein the insulating film is formed of boron phosphorus silicon glass, and the first material has an etching selectivity ratio of 100 or higher in relation to material that composes the etching stopper layer and material that composes the insulating film.

14. An electronic device, comprising:

a substrate on which a plurality of circuit areas are formed; and

an insulating layer formed on a first main surface of the substrate,

wherein at least one of the circuit areas is an inspection area that is independent of other circuits areas, and includes a conductive part and a contact hole, the conductive part being formed in the insulating film, and the contact hole neighboring a periphery of the conductive part.

15. The electronic device of Claim 14, wherein the conductive part includes a large-area portion that is inspected using an optical microscope.

16. The electronic device of Claim 15, wherein the inspection area is formed in a scribe area that is used as a cutting margin when cutting the other circuit areas from the substrate.

17. The electronic device of Claim 16, wherein the conductive part is composed of a material that has an etching selectivity ratio of 100 or higher in relation to a material that composes the insulating film.